

CSD25480F3 -20V P 沟道 FemtoFET™ MOSFET

1 特性

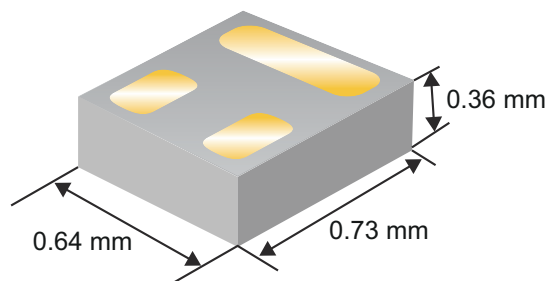
- 低导通电阻
- 超低 Q_g 和 Q_{gd}
- 超小尺寸
 - $0.73\text{mm} \times 0.64\text{mm}$
- 薄型封装
 - 最大厚度为 0.36mm
- 集成型 ESD 保护二极管
- 无铅且无卤素
- 符合 RoHS

2 应用

- 针对负载开关应用进行了优化
- 针对通用开关应用进行了优化
- 电池应用
- 手持式和移动类应用

3 说明

该 -20V、 $110\text{m}\Omega$ P 沟道 FemtoFET™ MOSFET 经过设计和优化，能够最大限度地减小在许多手持式和移动应用中占用的空间。这项技术能够在替代标准小信号 MOSFET 的同时大幅减小封装尺寸。



典型器件尺寸

产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
V_{DS}	漏源电压	-20	V
Q_g	栅极电荷总量 (-4.5V)	0.7	nC
Q_{gd}	栅极电荷 (栅极到漏极)	0.10	nC
$R_{DS(on)}$	漏源导通电阻	$V_{GS} = -1.8\text{V}$	420
		$V_{GS} = -2.5\text{V}$	203
		$V_{GS} = -4.5\text{V}$	132
		$V_{GS} = -8.0\text{V}$	110
$V_{GS(th)}$	阈值电压	-0.95	V

器件信息(1)

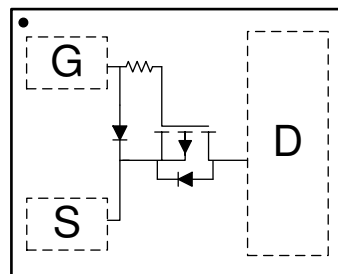
器件	数量	介质	封装	配送
CSD25480F3	3000	7 英寸卷带	Femto $0.73\text{mm} \times 0.64\text{mm}$ 基板栅格阵列 (LGA)	卷带包装
CSD25480F3T	250			

- (1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

绝对最大额定值

$T_A = 25^\circ\text{C}$ (除非另外注明)		值	单位
V_{DS}	漏源电压	-20	V
V_{GS}	栅源电压	-12	V
I_D	持续漏极电流 ⁽¹⁾	-1.7	A
I_{DM}	脉冲漏极电流 ^{(1) (2)}	-10.6	A
P_D	功率耗散 ⁽¹⁾	500	mW
$V_{(ESD)}$	人体放电模型 (HBM)	4000	V
	充电器件模型 (CDM)	2000	
T_J 、 T_{stg}	工作结温、贮存温度	-55 至 150	$^\circ\text{C}$

- (1) 安装在覆铜区域最小的 FR4 电路板上的典型 $R_{\theta JA} = 255^\circ\text{C/W}$ 。
- (2) 脉冲持续时间 $\leq 100\text{ }\mu\text{s}$ ，占空比 $\leq 1\%$ 。



顶视图



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4 Revision History

Changes from Revision A (August 2017) to Revision B (February 2022)	Page
• 将超薄型封装要点中的厚度从 0.35mm 更改为 0.36mm.....	1
• 将超薄型封装图片中的厚度从 0.35mm 更新为 0.36mm.....	1
• Changed ultra-low profile image height from 0.35 mm to 0.36 mm.....	8
• Added FemtoFET Surface Mount Guide note.....	9

Changes from Revision * (April 2016) to Revision A (August 2017)	Page
• Added the 节 6.1 section in 节 6	7
• Added Recommended Minimum PCB Layout	9
• Updated the 节 7.3	9

5 Specifications

5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _{DS} = - 250 μ A	- 20			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = - 16 V	- 50			nA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = - 12 V	- 25			nA
V _{GS(th)}	Gate-to-source threshold voltage	V _{DS} = V _{GS} , I _{DS} = - 250 μ A	- 0.70	- 0.95	- 1.20	V
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = - 1.8 V, I _{DS} = - 0.1 A	420		840	mΩ
		V _{GS} = - 2.5 V, I _{DS} = - 0.4 A	203		260	
		V _{GS} = - 4.5 V, I _{DS} = - 0.4 A	132		159	
		V _{GS} = - 8 V, I _{DS} = - 0.4 A	110		132	
g _{fs}	Transconductance	V _{DS} = - 10 V, I _{DS} = - 0.4 A	8.0			S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} = 0 V, V _{DS} = - 10 V, f = 1 MHz	119		155	pF
C _{oss}	Output capacitance		48		62	pF
C _{rss}	Reverse transfer capacitance		3.6		4.7	pF
R _G	Series gate resistance		16			Ω
Q _g	Gate charge total (- 4.5 V)	V _{DS} = - 10 V, I _{DS} = - 0.4 A	0.70		0.91	nC
Q _{gd}	Gate charge gate-to-drain		0.10			nC
Q _{gs}	Gate charge gate-to-source		0.26			nC
Q _{g(th)}	Gate charge at V _{th}		0.15			nC
Q _{oss}	Output charge	V _{DS} = - 10 V, V _{GS} = 0 V	1.3			nC
t _{d(on)}	Turnon delay time	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _{DS} = - 0.4 A, R _G = 10 Ω	9			ns
t _r	Rise time		5			ns
t _{d(off)}	Turnoff delay time		13			ns
t _f	Fall time		7			ns
DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	I _{SD} = - 0.4 A, V _{GS} = 0 V	- 0.78		- 1.0	V
Q _{rr}	Reverse recovery charge	V _{DS} = - 10 V, I _F = - 0.4 A, di/dt = 100 A/ μ s	1.2			nC
t _{rr}	Reverse recovery time		6.4			ns

5.2 Thermal Information

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		TYPICAL VALUES	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾	90	$^\circ\text{C}/\text{W}$
	Junction-to-ambient thermal resistance ⁽²⁾	255	

- (1) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz. (0.071-mm) thick Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

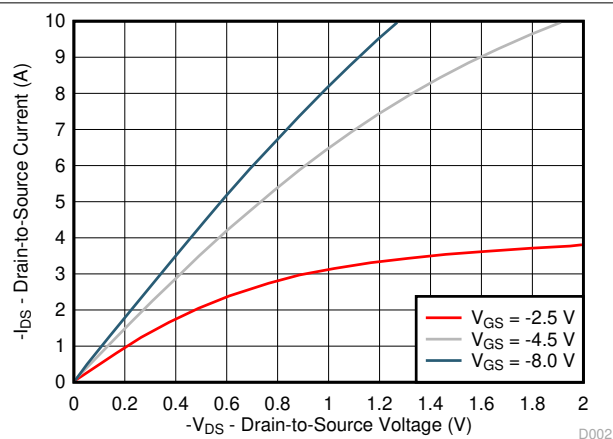


图 5-1. Saturation Characteristics

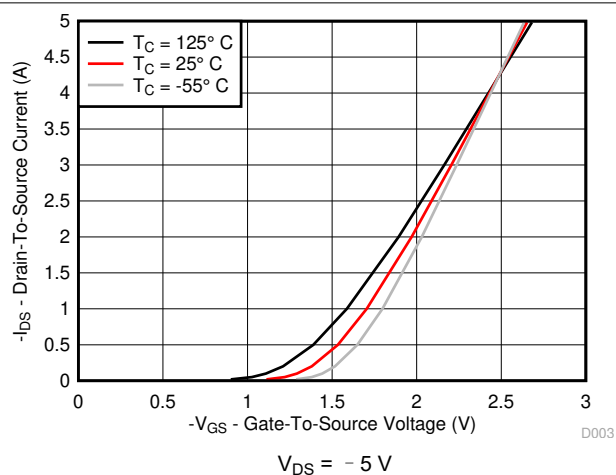


图 5-2. Transfer Characteristics

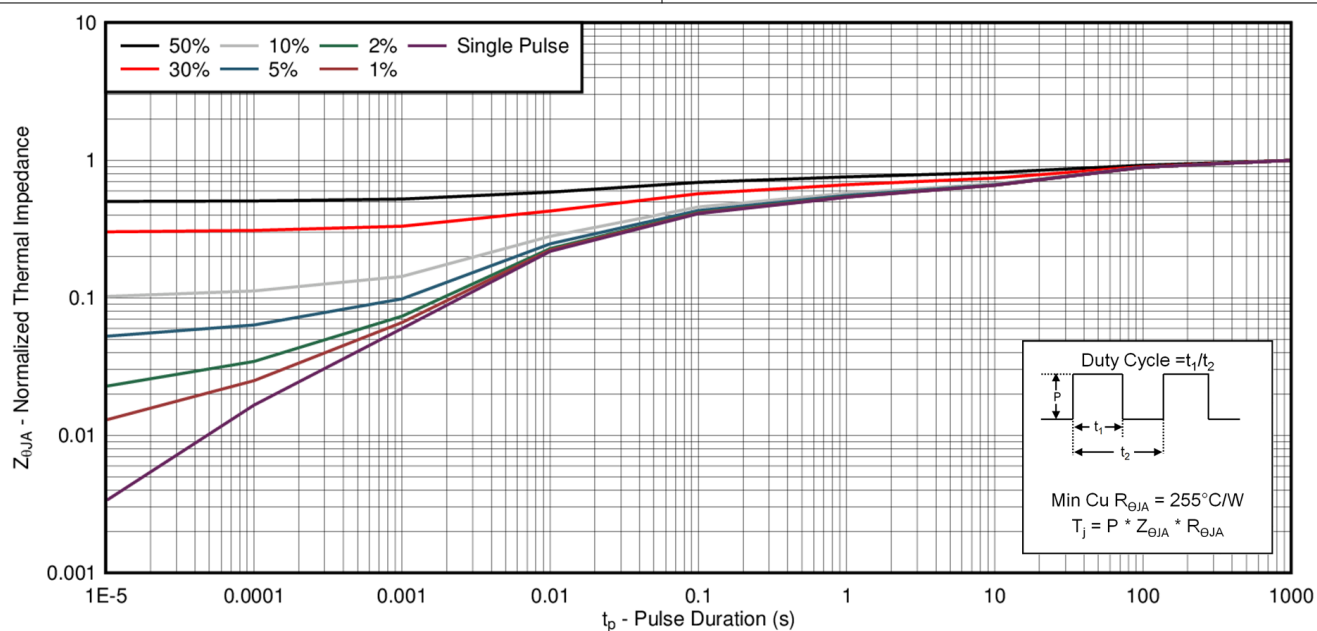


图 5-3. Transient Thermal Impedance

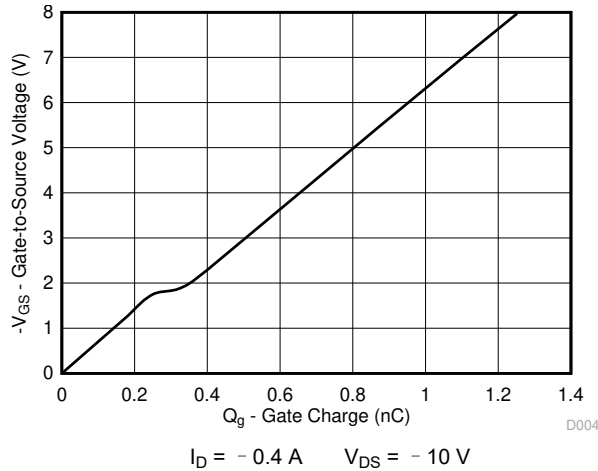


图 5-4. Gate Charge

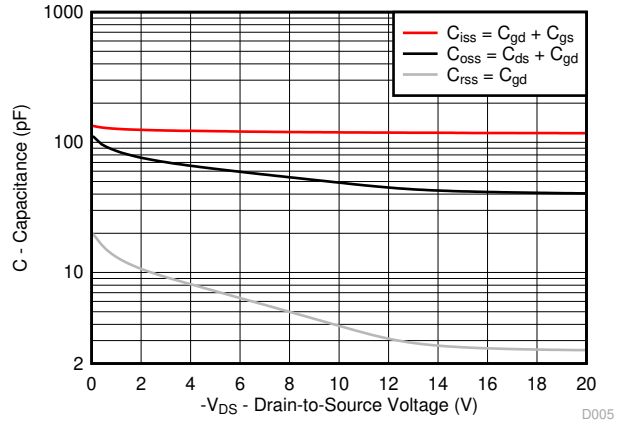


图 5-5. Capacitance

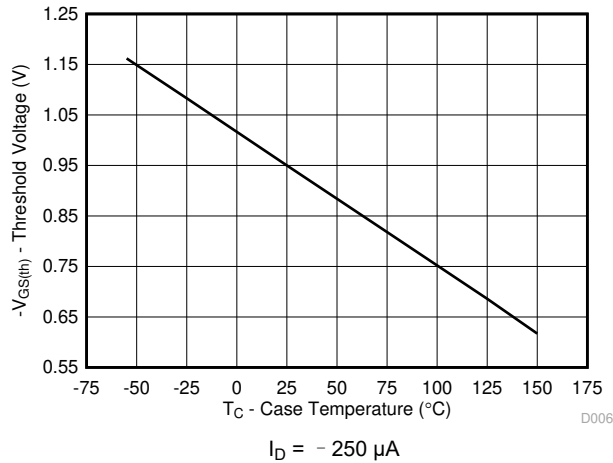


图 5-6. Threshold Voltage vs Temperature

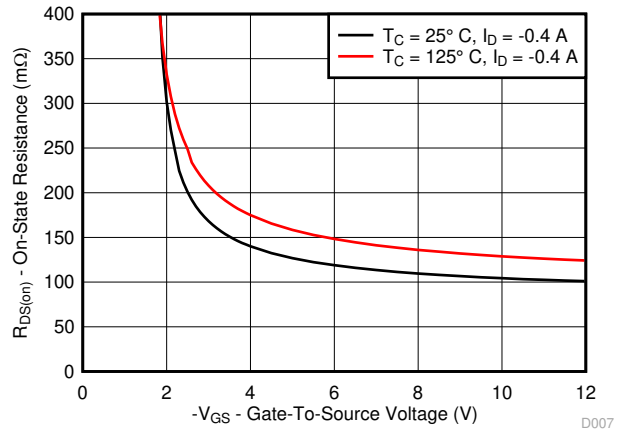


图 5-7. On-State Resistance vs Gate-to-Source Voltage

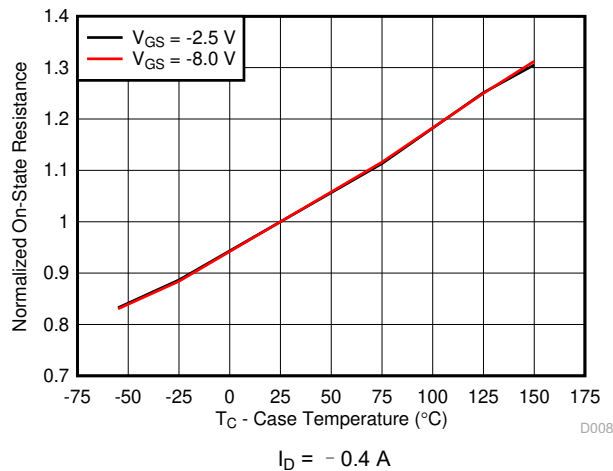


图 5-8. Normalized On-State Resistance vs Temperature

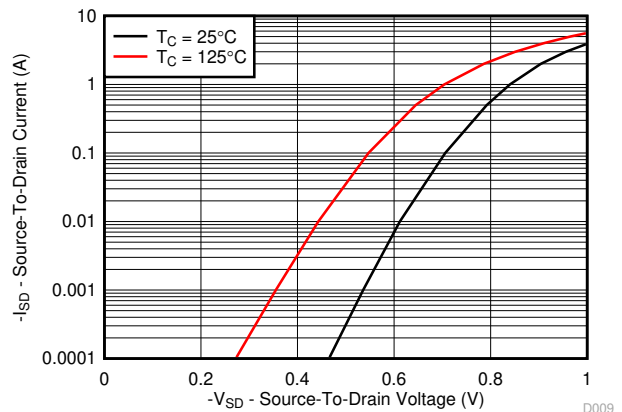


图 5-9. Typical Diode Forward Voltage

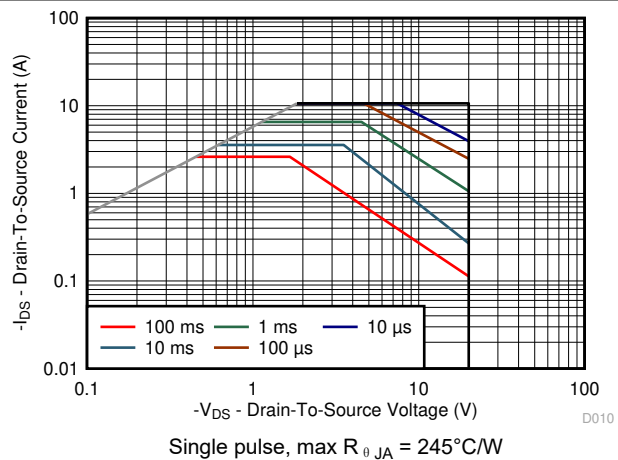


图 5-10. Maximum Safe Operating Area

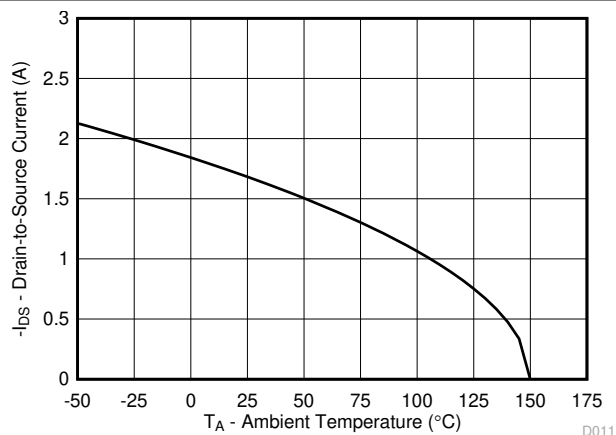


图 5-11. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Trademarks

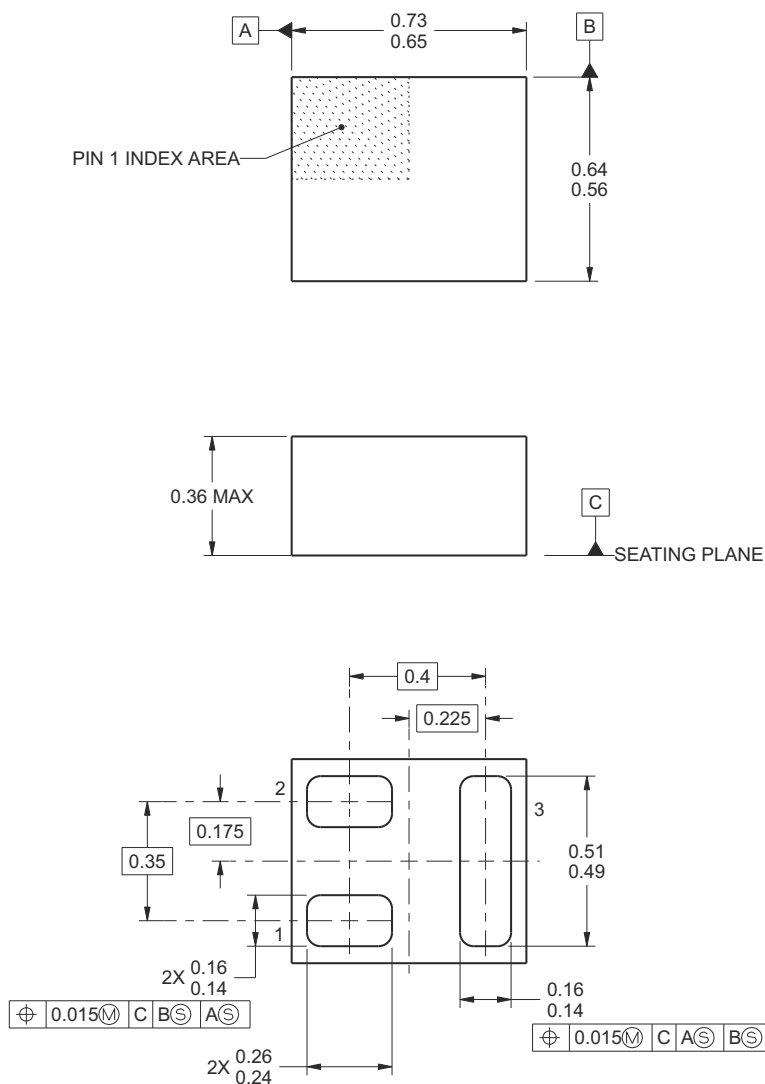
FemtoFET™ is a trademark of Texas Instruments.

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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

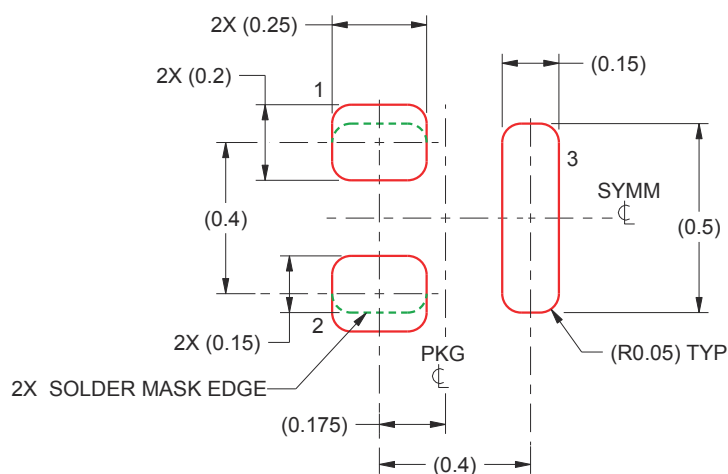
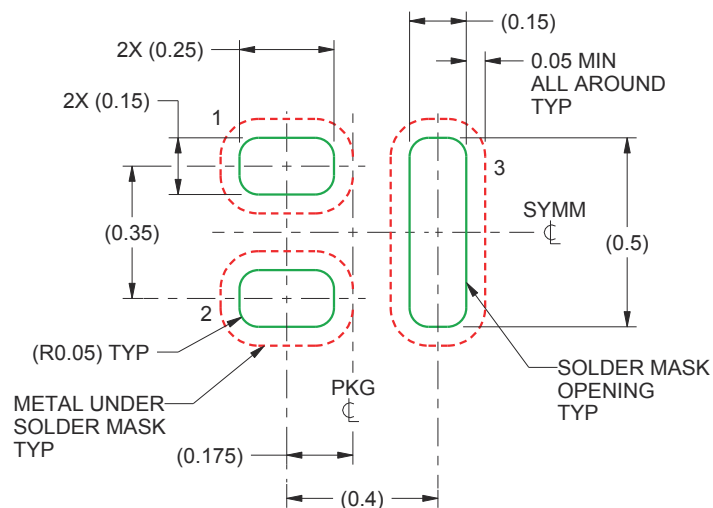
7.1 Mechanical Dimensions



- A. All linear dimensions are in millimeters (dimensions and tolerancing per ASME Y14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a lead-free solder land design.

表 7-1. Pin Configuration

POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain



TAPE AND REEL INFORMATION



*All dimensions are nominal

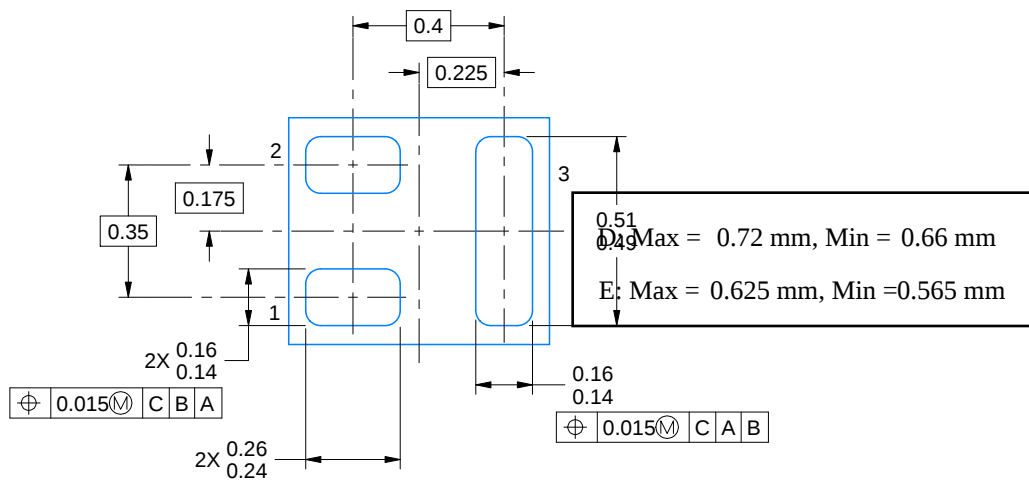
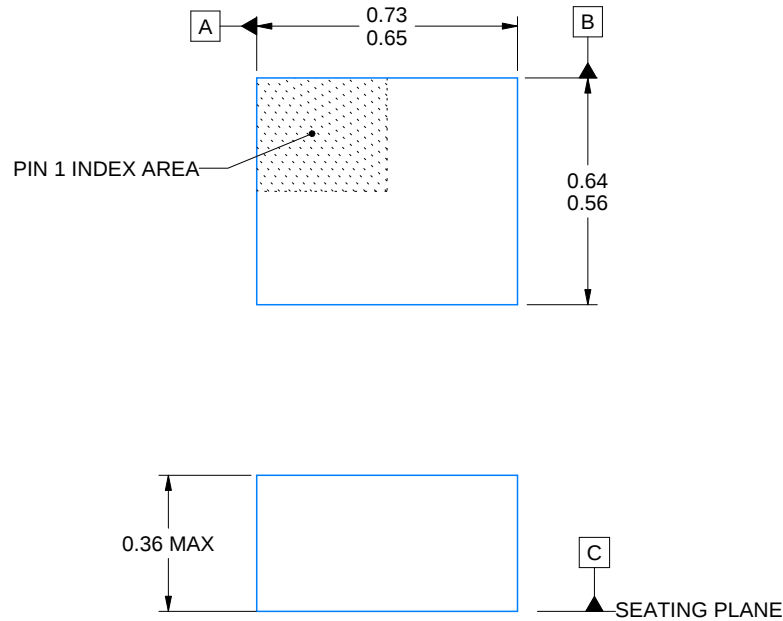
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25480F3	PICOSTAR	YJM	3	3000	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2
CSD25480F3T	PICOSTAR	YJM	3	250	180.0	8.4	1.94	0.79	0.44	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD25480F3	PICOSTAR	YJM	3	3000	182.0	182.0	20.0
CSD25480F3T	PICOSTAR	YJM	3	250	182.0	182.0	20.0

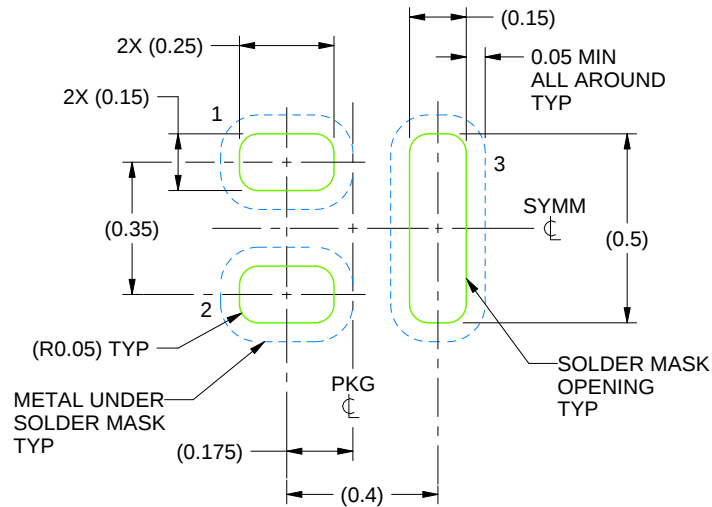


4222304/B 03/2022

NOTES:

PicoStar is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
2. This drawing is subject to change without notice.
3. This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device datasheet or contact a local TI representative.

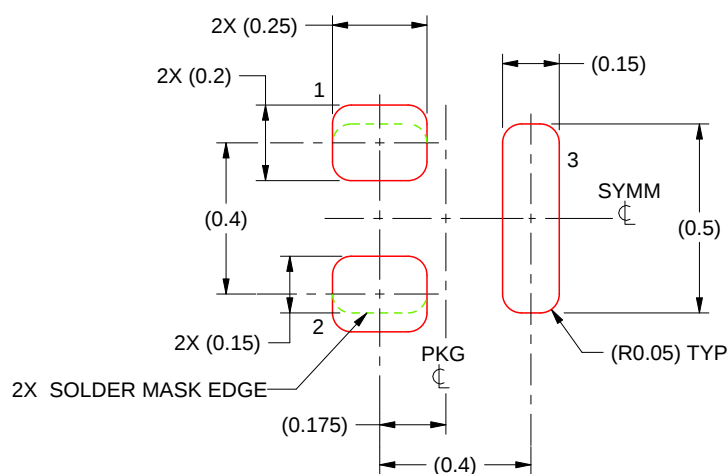


LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE:50X

4222304/B 03/2022

NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).



SOLDER PASTE EXAMPLE
 BASED ON 0.075 - 0.1 mm THICK STENCIL
 SCALE:50X

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NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要声明和免责声明

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